优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
60V	8.3mΩ @ V_{GS} = 10V	52.1A
	12.5mΩ @ V_{GS} = 4.5V	42.4A

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed

Description and Applications

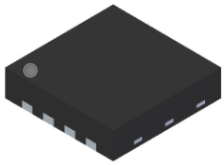
This new generation N-channel enhancement mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

- Synchronous Rectifier
- Power Management Functions
- DC-DC Converters

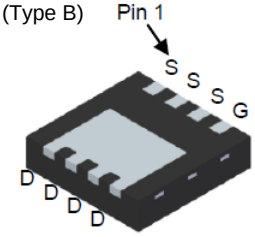
Mechanical Data

- Case: V-DFN3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Below Diagram
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.027 grams (Approximate)

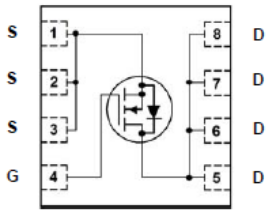
V-DFN3333-8 (Type B)



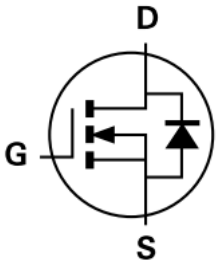
Top View



Bottom View



Top View
Internal Schematic



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 6)	Steady State	T_A = +25°C T_A = +70°C	I_D	14.6 11.7	A
Continuous Drain Current, V_{GS} = 10V (Note 7)		T_C = +25°C T_C = +70°C	I_D	52.1 41.7	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	208	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	52	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	208	A
Avalanche Current, L = 0.1mH			I_{AS}	27.4	A
Avalanche Energy, L = 0.1mH			E_{AS}	37.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.37	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	91	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.64	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	47.3	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	3.7	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 48V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.4	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.1	8.3	mΩ	V_{GS} = 10V, I_D = 13.5A
		—	8.7	12.5		V_{GS} = 4.5V, I_D = 11.5A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1406	—	pF	V_{DS} = 30V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	540	—		
Reverse Transfer Capacitance	C_{rss}	—	52	—		
Gate Resistance	R_g	—	1.85	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	28.4	—	nC	V_{DS} = 30V, I_D = 13.5A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	15.4	—		
Gate-Source Charge	Q_{gs}	—	2.4	—		
Gate-Drain Charge	Q_{gd}	—	9.0	—		
Turn-On Delay Time	$t_{D(ON)}$	—	10.5	—	ns	V_{DD} = 30V, V_{GS} = 10V, I_D = 13.5A, R_G = 6Ω
Turn-On Rise Time	t_R	—	49.0	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	30.9	—		
Turn-Off Fall Time	t_F	—	79.5	—		
Reverse Recovery Time	t_{RR}	—	26.7	—	ns	I_F = 13.5A, di/dt = 300A/µs
Reverse Recovery Charge	Q_{RR}	—	44.8	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

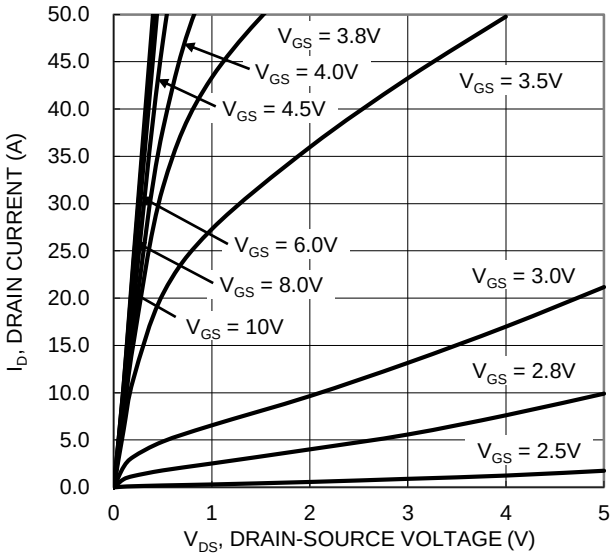


Figure 1. Typical Output Characteristic

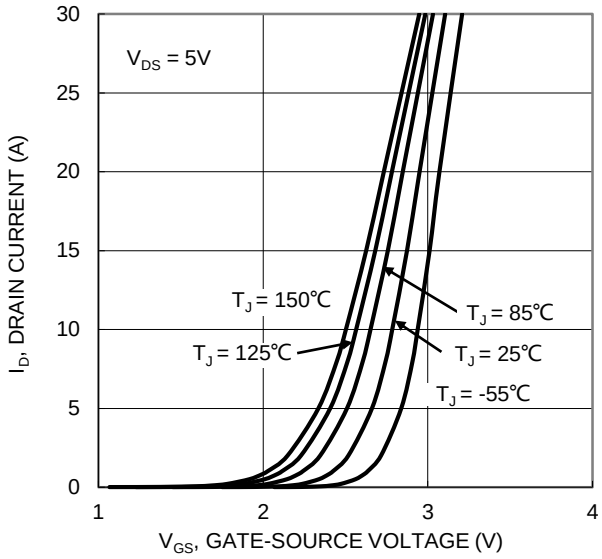


Figure 2. Typical Transfer Characteristic

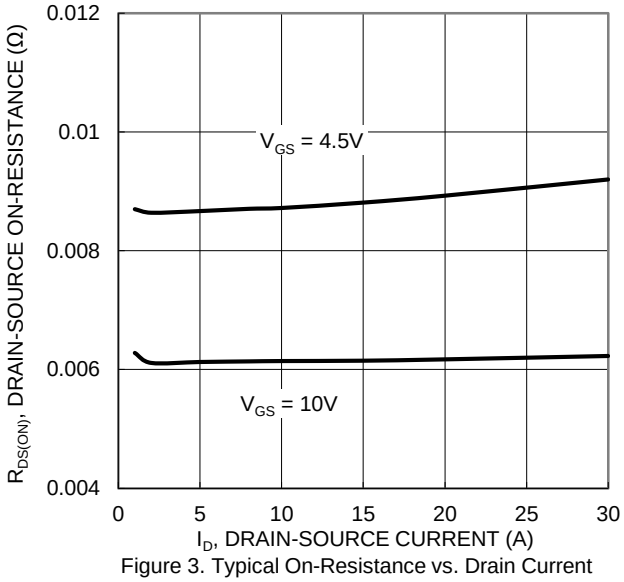


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

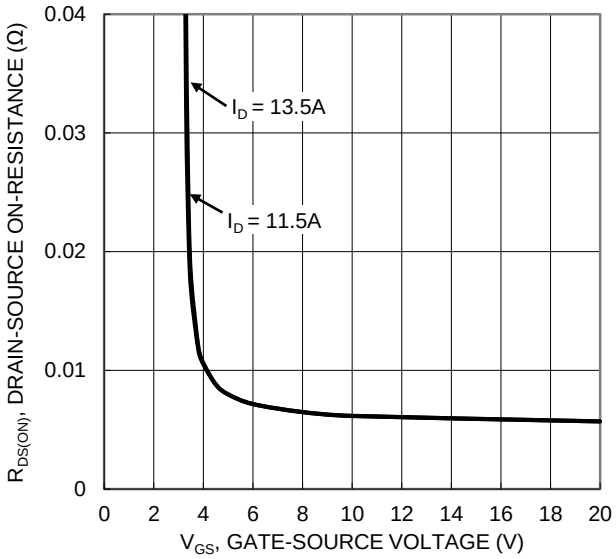


Figure 4. Typical Transfer Characteristic

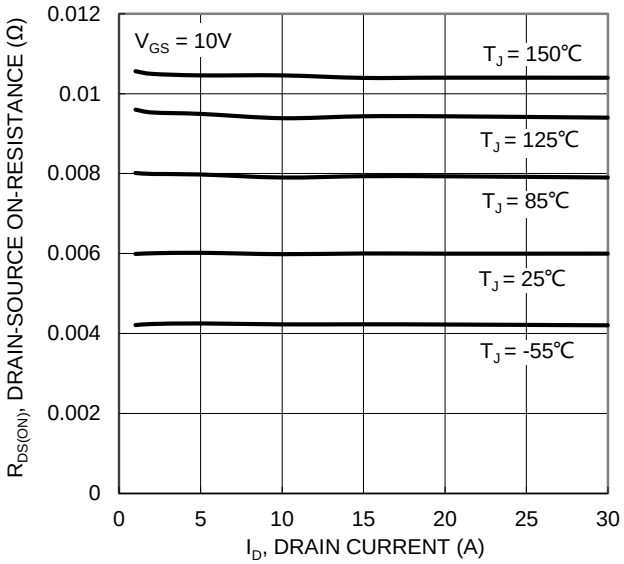


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

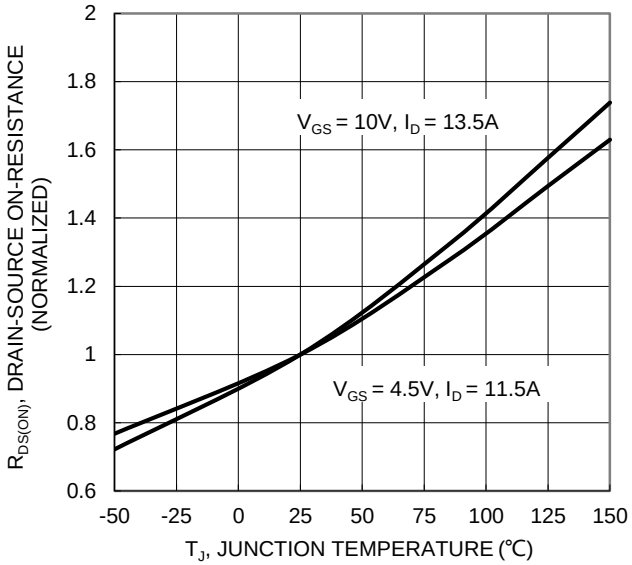


Figure 6. On-Resistance Variation with Junction Temperature

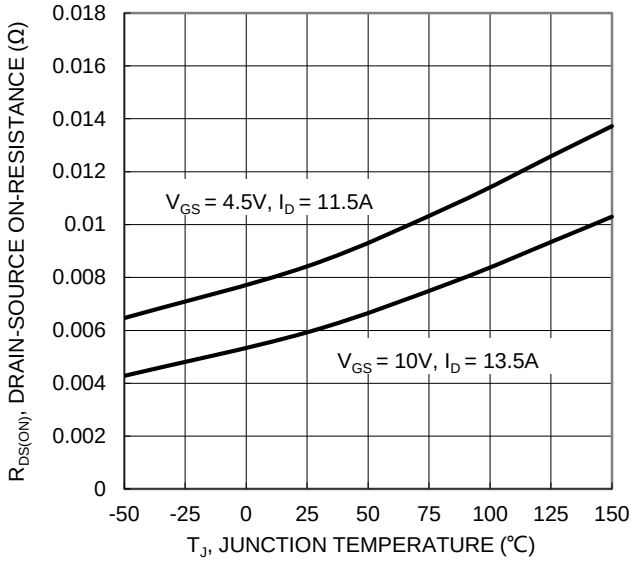


Figure 7. On-Resistance Variation with Junction Temperature

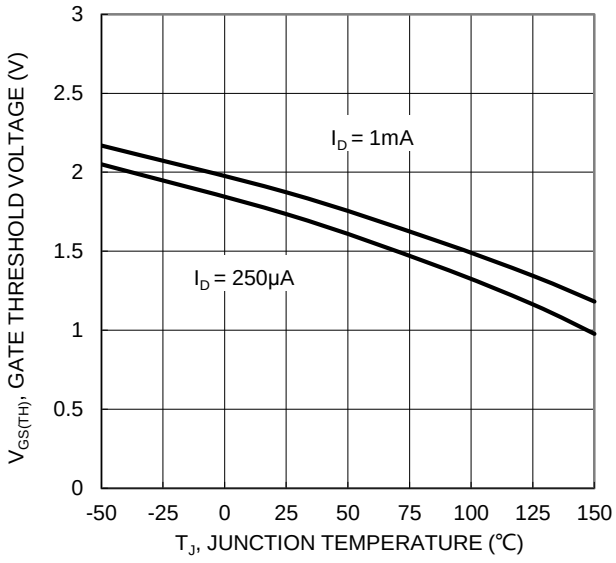


Figure 8. Gate Threshold Variation vs. Junction Temperature

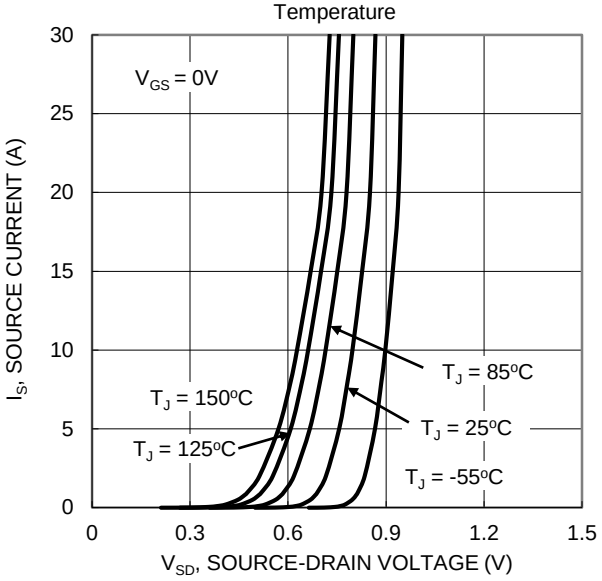


Figure 9. Diode Forward Voltage vs. Current

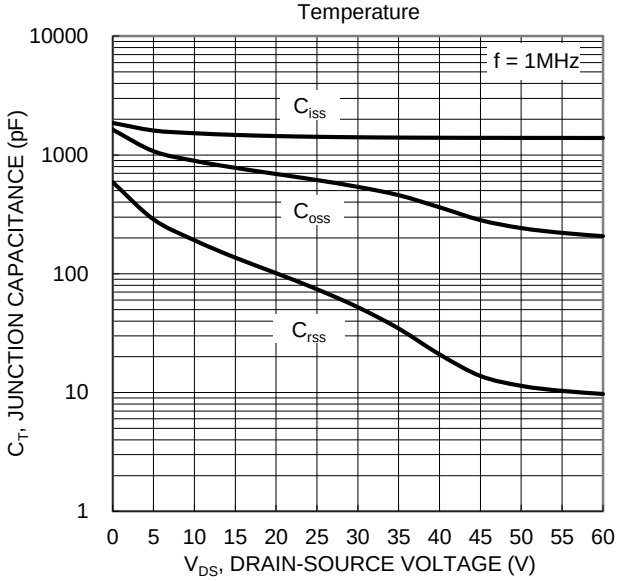


Figure 10. Typical Junction Capacitance

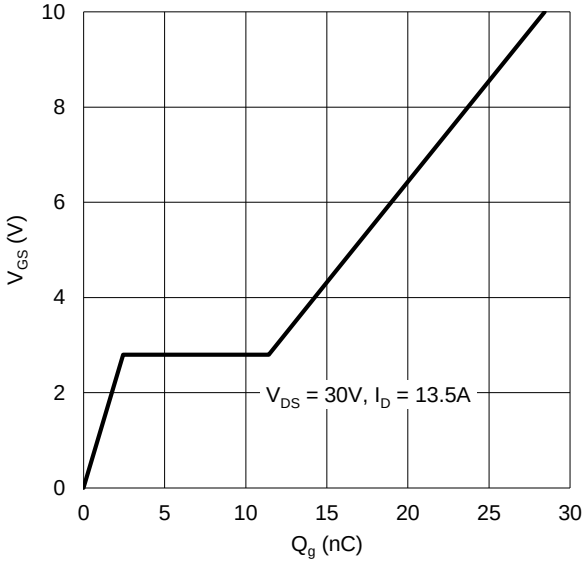


Figure 11. Gate Charge

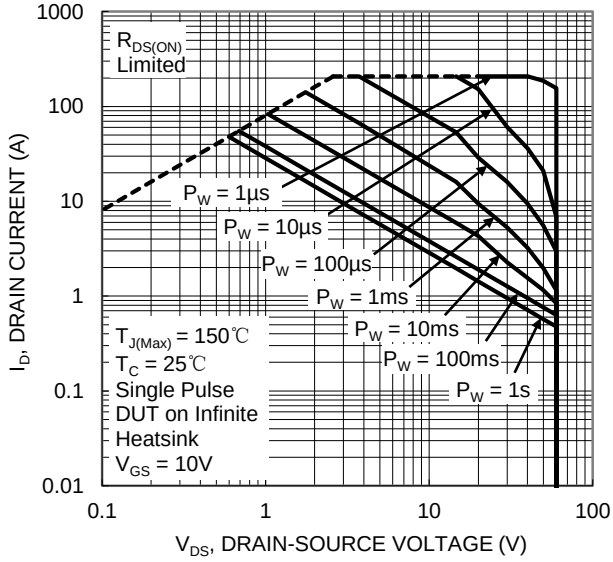


Figure 12. SOA, Safe Operation Area

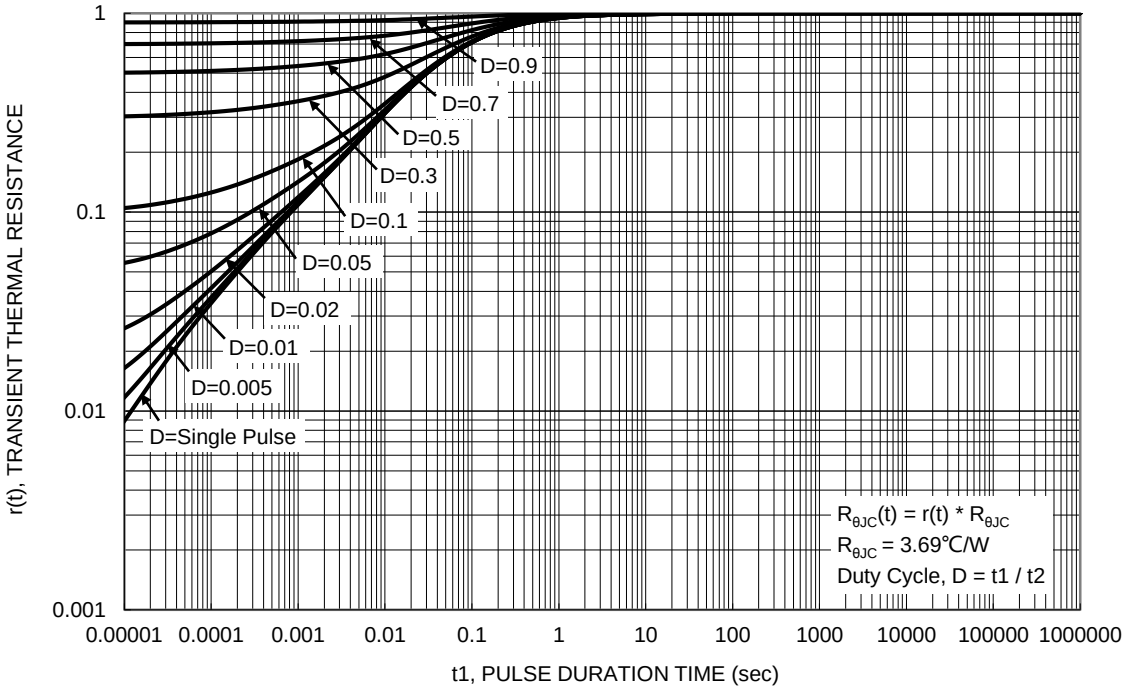
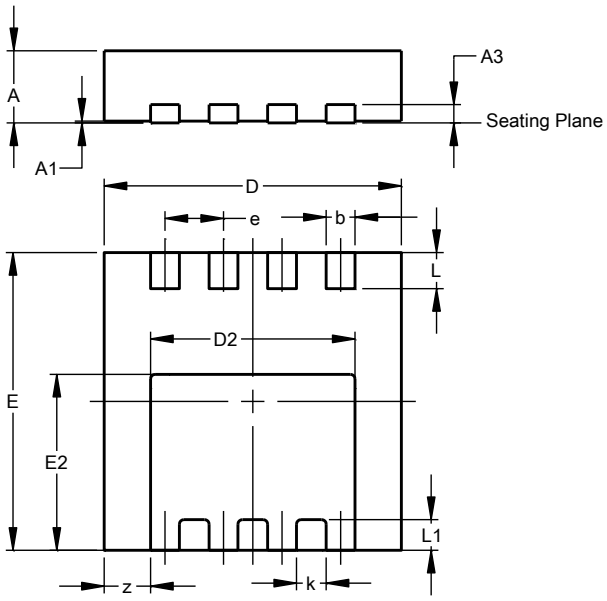


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

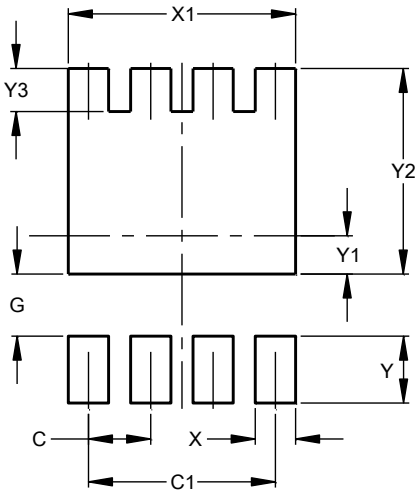
V-DFN3333-8 (Type B)



V-DFN3333-8 (Type B)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	--	--	0.203
b	0.27	0.37	0.32
D	3.25	3.35	3.30
D2	2.17	2.37	2.27
E	3.25	3.35	3.30
E2	1.85	2.05	1.95
e	--	--	0.65
k	--	--	0.33
L	0.35	0.45	0.40
L1	--	--	0.34
z	--	--	0.515
All Dimensions in mm			

Suggested Pad Layout

V-DFN3333-8 (Type B)



Dimensions	Value (in mm)
C	0.650
C1	1.950
G	0.650
X	0.420
X1	2.370
Y	0.700
Y1	0.400
Y2	2.150
Y3	0.450